L Number	Hits	Search Text	DB	Time stamp
12	112	(defect same ((low$2 less$5) with reflect$5)) and ((wafer substrate) with (defect particle)) and mask	USPAT; US-PGPUB; EPO; JPO	2003/03/06 19:47
44	791	((wafer substrate target) near10 (defect particle contamin$5 foreign)) and (defect with pinhole)	USPAT; US-PGPUB; EPO; JPO	2003/03/06 20:35
45	42	(((wafer substrate target) near10 (defect particle contamin$5 foreign)) and (defect with pinhole)) and (defect with ((foreign adj particle) dust))	USPAT; US-PGPUB; EPO; JPO	2003/03/06 20:37
46	39	((((wafer substrate target) near10 (defect particle contamin$5 foreign)) and (defect with pinhole)) and (defect with ((foreign adj particle) dust))) and (defect with (mask substrate))	USPAT; US-PGPUB; EPO; JPO	2003/03/06 20:38
48	255	mask and ((defect with substrate) same repair$3)	USPAT; US-PGPUB; EPO; JPO	2003/03/06 21:08
49	2	(mask and ((defect with substrate) same repair$3)) and (low adj reflect$5)	USPAT; US-PGPUB; EPO; JPO	2003/03/06 20:44
-	647	(356/399).CCLS.	USPAT; US-PGPUB; EPO; JPO	2003/03/05 10:52
-	99	((356/399).CCLS.) and (defect imperfect$4 scratch$2 dust particle)	USPAT; US-PGPUB; EPO; JPO	2003/03/05 10:54
-	309	(356/237.5).CCLS.	USPAT; US-PGPUB; EPO; JPO	2003/03/05 14:31
-	3	((356/237.5).CCLS.) and 356/400.ccls.	USPAT; US-PGPUB; EPO; JPO	2003/03/05 14:37
-	18	(356/$.ccls. and ((defect with substrate) same (pattern with position))) and mask	USPAT; US-PGPUB; EPO; JPO	2003/03/05 14:57
-	58	mask and ((defect with substrate) same (pattern with position))	USPAT; US-PGPUB; EPO; JPO	2003/03/05 17:19
-	2673	(356/237.1,237.2,237.3,237.4,237.6).CCLS.	USPAT; US-PGPUB; EPO; JPO	2003/03/05 16:23
-	38	((356/237.1,237.2,237.3,237.4,237.6).CCLS.) and (defect with substrate) and (defect same (pattern with (shift position)))	USPAT; US-PGPUB; EPO; JPO	2003/03/05 16:34
-	111	(356/620).CCLS.	USPAT; US-PGPUB; EPO; JPO	2003/03/05 16:55
-	9	((356/620).CCLS.) and defect	USPAT; US-PGPUB; EPO; JPO	2003/03/05 16:58
-	1317	(250/559.41,559.45,559.4).CCLS.	USPAT; US-PGPUB; EPO; JPO	2003/03/05 16:58
-	466	((250/559.41,559.45,559.4).CCLS.) and defect	USPAT; US-PGPUB; EPO; JPO	2003/03/05 16:58
-	11	((250/559.41,559.45,559.4).CCLS.) and (defect with substrate) and (defect same (pattern with position))	USPAT; US-PGPUB; EPO; JPO	2003/03/05 16:59
-	192	mask and ((defect with substrate) same (defect with position))	USPAT; US-PGPUB; EPO; JPO	2003/03/06 09:56
-	168	(((356/$.ccls. 355/$.ccls. 430/$.ccls. 250/$.ccls.) and ((detect$4 sens$4) near7 ((wafer substrate target) near8 (foreign contamin$5 defect$3 particle)))) and (mask reticle)) and ((detect$4 sens$4) adj6 (defect$4) adj4 (wafer substrate))	USPAT; US-PGPUB; EPO; JPO	2003/03/06 13:31

-	4289	((356/237.2) or (250/461.1,459.1) or (355/30,53)).CCLS.	USPAT; US-PGPUB; EPO; JPO	2003/03/06 12:38
-	705	(((356/237.2) or (250/461.1,459.1) or (355/30,53)).CCLS.) and defect	USPAT; US-PGPUB; EPO; JPO	2003/03/06 12:38
-	303	((((356/237.2) or (250/461.1,459.1) or (355/30,53)).CCLS.) and defect) and ((wafer substrate target) with (foreign contamin$5 defect particle))	USPAT; US-PGPUB; EPO; JPO	2003/03/06 12:40
-	151	(((((356/237.2) or (250/461.1,459.1) or (355/30,53)).CCLS.) and defect) and ((wafer substrate target) with (foreign contamin$5 defect particle))) and ((mask pattern reticle) with (position shift$3))	USPAT; US-PGPUB; EPO; JPO	2003/03/06 12:44
-	118	(((356/$.ccls. 355/$.ccls. 430/$.ccls. 250/$.ccls.) and ((detect$4 sens$4) near7 ((wafer substrate target) near8 (foreign contamin$5 defect$3 particle)))) and (mask reticle)) and ((detect$4 sens$4) adj6 (defect$4) adj4 (wafer substrate))	USPAT; EPO; JPO	2003/03/06 13:40
-	237	((356/$.ccls. 355/$.ccls. 430/$.ccls. 250/$.ccls.) and ((wafer substrate target) near8 (foreign contamin$5 defect$3 particle))) and ((position with defect) same(wafer substrate))	USPAT; EPO; JPO	2003/03/06 13:41
-	237	((356/$.ccls. 355/$.ccls. 430/$.ccls. 250/$.ccls.) and ((wafer substrate target) near8 (foreign contamin$5 defect$3 particle))) and ((position with defect) same (wafer substrate))	USPAT; EPO; JPO	2003/03/06 13:44
-	136	(((356/$.ccls. 355/$.ccls. 430/$.ccls. 250/$.ccls.) and ((wafer substrate target) near8 (foreign contamin$5 defect$3 particle))) and ((position with defect) same (wafer substrate))) and (mask reticle)	USPAT; EPO; JPO	2003/03/06 13:42
-	105	((((356/$.ccls. 355/$.ccls. 430/$.ccls. 250/$.ccls.) and ((wafer substrate target) near8 (foreign contamin$5 defect$3 particle))) and ((position with defect) same (wafer substrate))) and (mask reticle)) and ((mask reticle) same defect)	USPAT; EPO; JPO	2003/03/06 13:42
-	203	((356/$.ccls. 355/$.ccls. 430/$.ccls. 250/$.ccls.) and ((wafer substrate target) near8 (foreign contamin$5 defect$3 particle))) and ((reticle mask photomask) and (((wafer substrate) with defect) same position))	USPAT; US-PGPUB; EPO; JPO	2003/03/06 14:07
-	4	(mask adj blank) same (defect with position)	USPAT; US-PGPUB; EPO; JPO	2003/03/06 14:53